THE THERMODYNAMIC ASPECTS OF A MODEL OF FORMATION OF MICRODEFECTS IN SEMICONDUCTOR SILICON

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S u m m a r y

The thermodynamic calculation of main characteristic parameters which describe the processes of recombination of intrinsic point defects in semiconductor silicon is carried out. It is shown that the recombination rate is low because of the presence of the entropy barrier. It is confirmed that the disintegration of a solid solution of intrinsic point defects happens simultaneously by two mechanisms: vacancy and interstitial ones.